



Product Summary

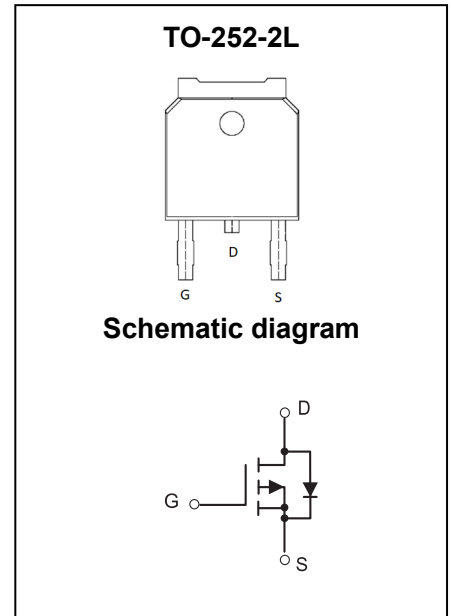
$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
-30V	5.5mΩ@-10V	-65A
	8.8mΩ@-4.5V	

Feature

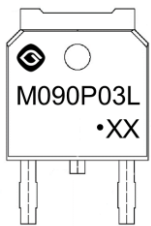
- Trench Technology Power MOSFET
- Low $R_{DS(ON)}$
- Low Gate Charge
- Low Gate Resistance
- 100% UIS Tested
- 100% ΔV_{DS} Tested

Application

- Power Switching Application



MARKING:



M090P03L = Device Code
 XX = Date Code
 Solid Dot = Green Indicator

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain - Source Voltage		V_{DS}	-30	V
Gate - Source Voltage		V_{GS}	± 20	V
Continuous Drain Current ¹	$T_C = 25^\circ\text{C}$	I_D	-65	A
Continuous Drain Current ¹	$T_C = 100^\circ\text{C}$	I_D	-55	A
Continuous Drain Current ⁶	$T_A = 25^\circ\text{C}$	I_D	-15	A
Pulsed Drain Current ²		I_{DM}	-280	A
Single Pulsed Avalanche Current ³		I_{AS}	-40	A
Single Pulsed Avalanche Energy ³		E_{AS}	400	mJ
Power Dissipation ⁵	$T_C = 25^\circ\text{C}$	P_D	78	W
Thermal Resistance from Junction to Ambient ⁶		$R_{\theta JA}$	50	$^\circ\text{C}/\text{W}$
Thermal Resistance from Junction to Case		$R_{\theta JC}$	1.6	$^\circ\text{C}/\text{W}$
Junction Temperature		T_J	150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55~ +150	$^\circ\text{C}$

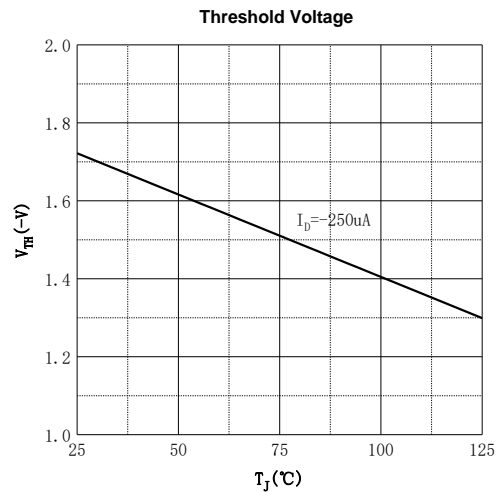
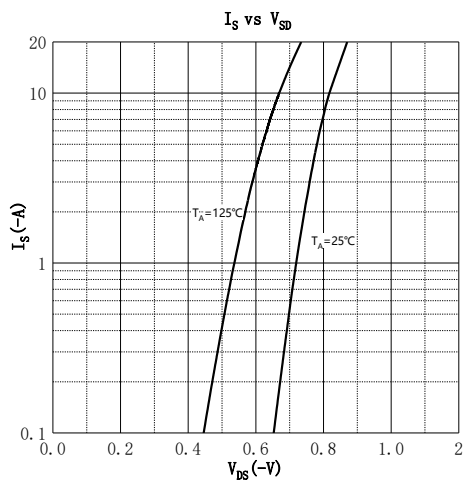
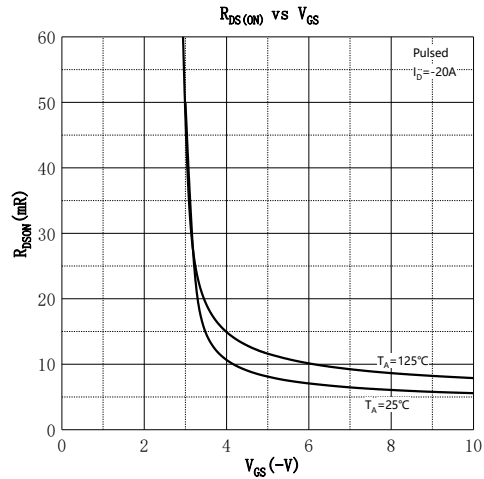
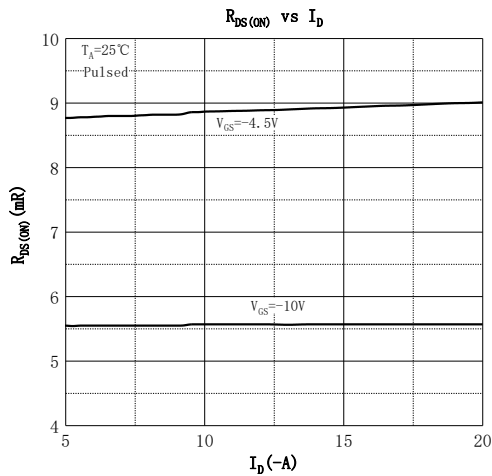
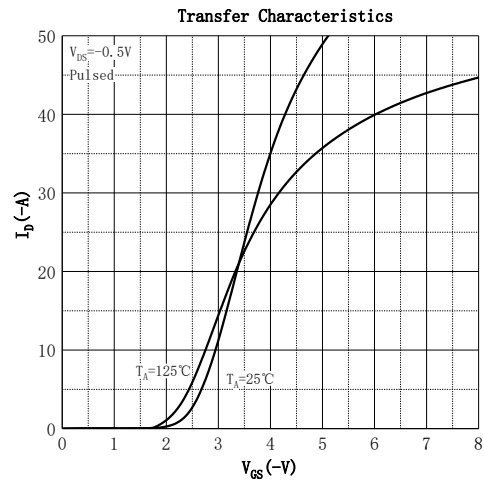
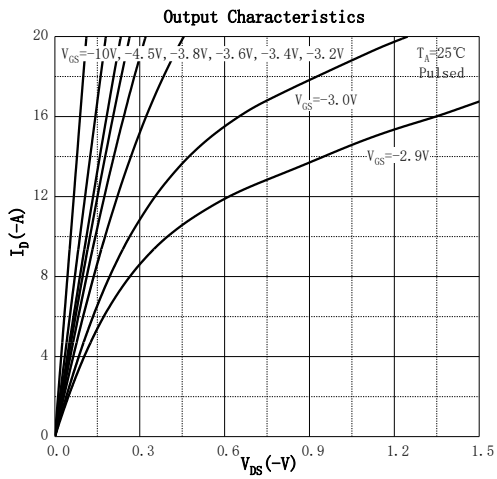
MOSFET ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

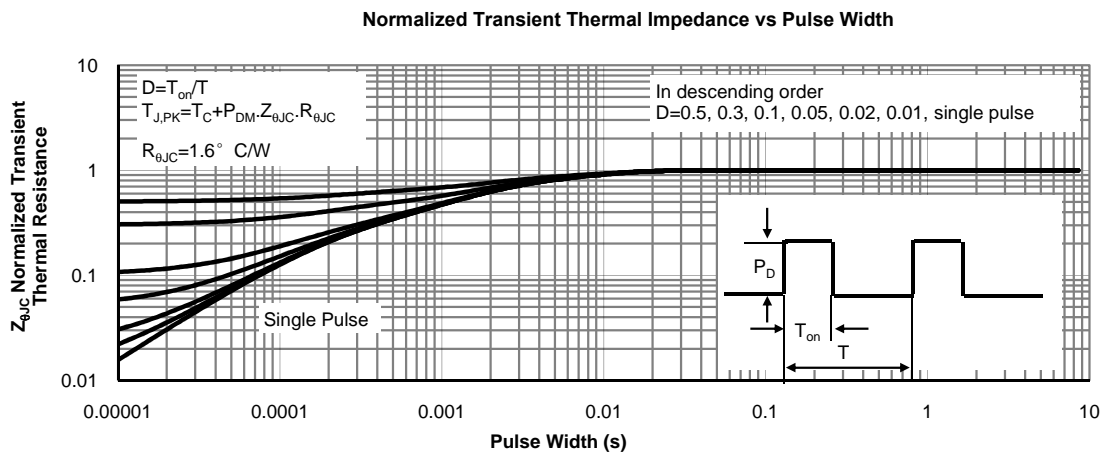
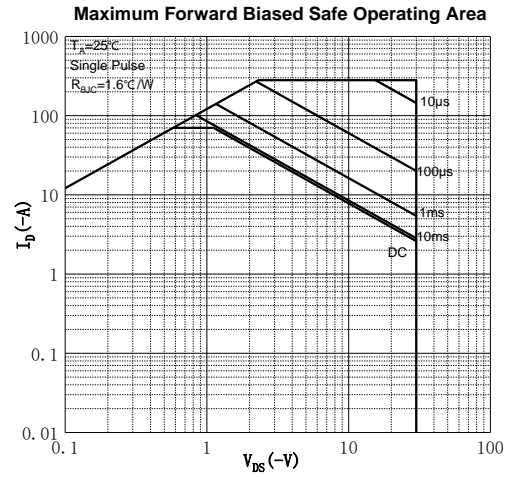
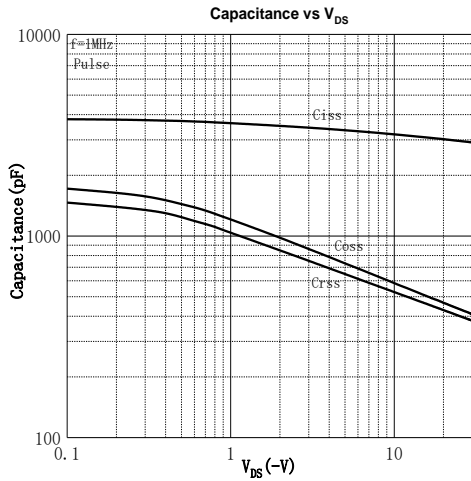
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain - Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-30			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -30V, V_{GS} = 0V$			-1	μA
Gate - Body Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 100	nA
On Characteristics⁴						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-1	-1.7	-3	V
Drain-source On-resistance	$R_{DS(on)}$	$V_{GS} = -10V, I_D = -20A$		5.5	7.4	m Ω
		$V_{GS} = -4.5V, I_D = -10A$		8.8	14	
Forward Transconductance	g_{FS}	$V_{DS} = -5V, I_D = -10A$		25		S
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS} = -15V, V_{GS} = 0V, f = 1MHz$		3141		pF
Output Capacitance	C_{oss}			526		
Reverse Transfer Capacitance	C_{rss}			481		
Gate Resistance	R_g	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$		4.5		Ω
Switching Characteristics						
Total Gate Charge	Q_g	$V_{DS} = -15V, V_{GS} = -10V, I_D = -20A$		64.5		nC
Gate-source Charge	Q_{gs}			7.6		
Gate-drain Charge	Q_{gd}			13.8		
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = -15V, V_{GS} = -10V,$ $R_L = 0.75\Omega, R_G = 3\Omega$		17		ns
Turn-on Rise Time	t_r			11		
Turn-off Delay Time	$t_{d(off)}$			46		
Turn-off Fall Time	t_f			21		
Source - Drain Diode Characteristics						
Diode Forward Voltage ⁴	V_{SD}	$V_{GS} = 0V, I_S = -20A$			-1.2	V

Notes :

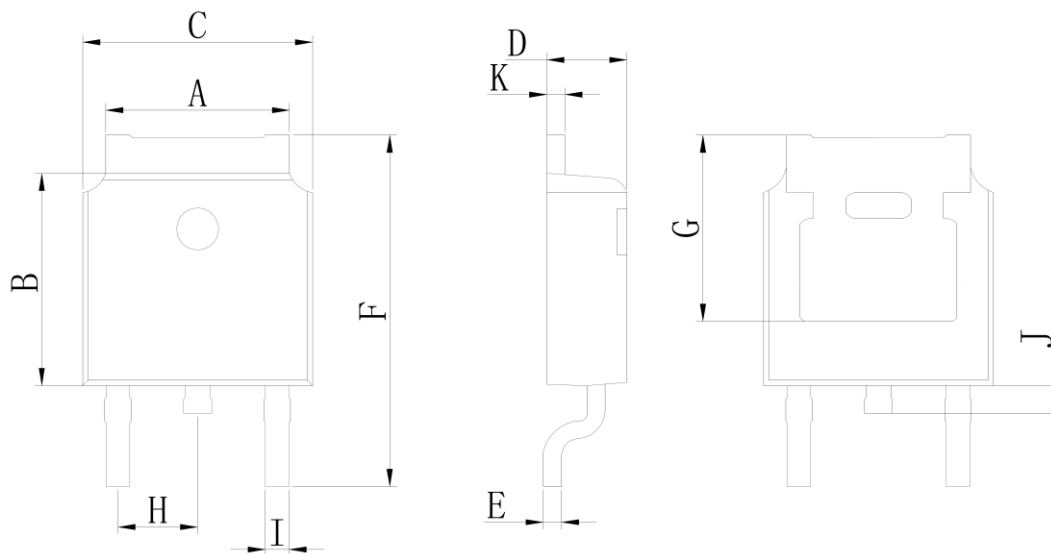
- 1.The maximum current rating is limited by package.And device mounted on a large heatsink
- 2.Pulse Test : Pulse Width $\leq 10\mu s$, duty cycle $\leq 1\%$.
- 3.EAS condition: $V_{DD} = -15V, V_{GS} = -10V, L = 0.5mH, R_G = 25\Omega$ Starting $T_J = 25^\circ\text{C}$.
- 4.Pulse Test : Pulse Width $\leq 300\mu s$, duty cycle $\leq 2\%$.
- 5.The power dissipation P_D is limited by $T_{J(MAX)} = 150^\circ\text{C}$.And device mounted on a large heatsink
- 6.Device mounted on $1in^2$ FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$.

Typical Characteristics





TO-252-2L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	5.050	5.650	0.199	0.222
B	5.800	6.400	0.228	0.252
C	6.250	6.850	0.246	0.270
D	2.200	2.400	0.087	0.094
E	0.400	0.600	0.016	0.024
F	9.710	10.310	0.382	0.406
G	5.050	5.650	0.199	0.222
H	2.100	2.500	0.083	0.098
I	0.700	0.900	0.028	0.035
J	0.500	0.900	0.020	0.035
K	0.400	0.600	0.016	0.024